



Is Now Part of



**ON Semiconductor®**

To learn more about ON Semiconductor, please visit our website at  
[www.onsemi.com](http://www.onsemi.com)

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.



November 2015

# MOC3081M, MOC3082M, MOC3083M 6-Pin DIP Zero-Cross Triac Driver Optocoupler (800 Volt Peak)

## Features

- Simplifies Logic Control of 240 VAC Power
- Zero Voltage Crossing to Minimize Conducted and Radiated Line Noise
- 800 V Peak Blocking Voltage
- Superior Static  $dv/dt$ 
  - 1500 V/ $\mu$ s Typical, 600 V/ $\mu$ s Guaranteed
- Safety and Regulatory Approvals
  - UL1577, 4,170 VAC<sub>RMS</sub> for 1 Minute
  - DIN EN/IEC60747-5-5

## Applications

- Solenoid/Valve Controls
- Lighting Controls
- Static Power Switches
- AC Motor Starters
- Temperature Controls
- E.M. Contactors
- AC Motor Drives
- Solid State Relays

## Description

The MOC3081M, MOC3082M and MOC3083M devices consist of a GaAs infrared emitting diode optically coupled to a monolithic silicon detector performing the function of a zero voltage crossing bilateral triac driver.

They are designed for use with a discrete power triac in the interface of logic systems to equipment powered from 240 VAC lines, such as solid-state relays, industrial controls, motors, solenoids and consumer appliances, etc.

## Schematic

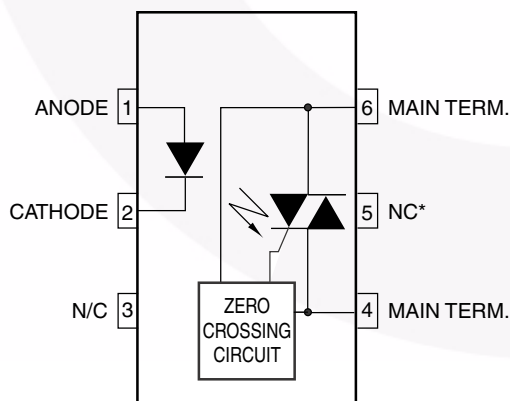


Figure 1. Schematic

## Package Outlines

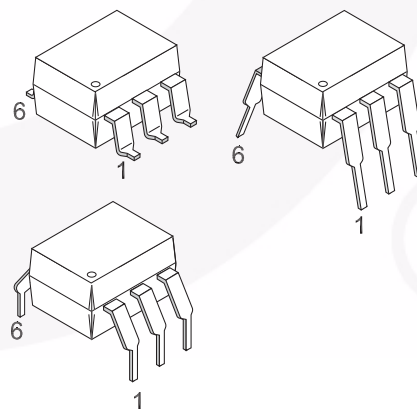


Figure 2. Package Outlines

MOC3081M, MOC3082M, MOC3083M — 6-Pin DIP Zero-Cross Triac Driver Optocoupler (800 Volt Peak)

## Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for “safe electrical insulation” only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter		Characteristics
Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated Mains Voltage	< 150 V <sub>RMS</sub>	I–IV
	< 300 V <sub>RMS</sub>	I–IV
Climatic Classification		40/85/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
V <sub>PR</sub>	Input-to-Output Test Voltage, Method A, V <sub>IORM</sub> × 1.6 = V <sub>PR</sub> , Type and Sample Test with t <sub>m</sub> = 10 s, Partial Discharge < 5 pC	1360	V <sub>peak</sub>
	Input-to-Output Test Voltage, Method B, V <sub>IORM</sub> × 1.875 = V <sub>PR</sub> , 100% Production Test with t <sub>m</sub> = 1 s, Partial Discharge < 5 pC	1594	V <sub>peak</sub>
V <sub>IORM</sub>	Maximum Working Insulation Voltage	850	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	6000	V <sub>peak</sub>
	External Creepage	≥ 7	mm
	External Clearance	≥ 7	mm
	External Clearance (for Option TV, 0.4" Lead Spacing)	≥ 10	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
R <sub>IO</sub>	Insulation Resistance at T <sub>S</sub> , V <sub>IO</sub> = 500 V	> 10 <sup>9</sup>	Ω

## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.  $T_A = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	Value	Unit
<b>TOTAL DEVICE</b>			
$T_{\text{STG}}$	Storage Temperature	-40 to +150	$^\circ\text{C}$
$T_{\text{OPR}}$	Operating Temperature	-40 to +85	$^\circ\text{C}$
$T_J$	Junction Temperature Range	-40 to +100	$^\circ\text{C}$
$T_{\text{SOL}}$	Lead Solder Temperature	260 for 10 seconds	$^\circ\text{C}$
$P_D$	Total Device Power Dissipation at $25^\circ\text{C}$ Ambient	250	mW
	Derate Above $25^\circ\text{C}$	2.94	mW/ $^\circ\text{C}$
<b>EMITTER</b>			
$I_F$	Continuous Forward Current	60	mA
$V_R$	Reverse Voltage	6	V
$P_D$	Total Power Dissipation at $25^\circ\text{C}$ Ambient	120	mW
	Derate Above $25^\circ\text{C}$	1.41	mW/ $^\circ\text{C}$
<b>DETECTOR</b>			
$V_{\text{DRM}}$	Off-State Output Terminal Voltage	800	V
$I_{\text{TSM}}$	Peak Non-Repetitive Surge Current (Single Cycle 60 Hz Sine Wave)	1	A
$P_D$	Total Power Dissipation at $25^\circ\text{C}$ Ambient	150	mW
	Derate Above $25^\circ\text{C}$	1.76	mW/ $^\circ\text{C}$

## Electrical Characteristics

$T_A = 25^\circ\text{C}$  unless otherwise specified.

### Individual Component Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>EMITTER</b>						
$V_F$	Input Forward Voltage	$I_F = 30\text{ mA}$		1.3	1.5	V
$I_R$	Reverse Leakage Current	$V_R = 6\text{ V}$		0.005	100	$\mu\text{A}$
<b>DETECTOR</b>						
$I_{\text{DRM1}}$	Peak Blocking Current, Either Direction	$V_{\text{DRM}} = 800\text{ V}$ , $I_F = 0^{(1)}$		10	500	nA
dv/dt	Critical Rate of Rise of Off-State Voltage	$I_F = 0$ (Figure 11) <sup>(2)</sup>	600	1500		V/ $\mu\text{s}$

### Transfer Characteristics

Symbol	Parameter	Test Conditions	Device	Min.	Typ.	Max.	Unit
$I_{\text{FT}}$	LED Trigger Current (Rated $I_{\text{FT}}$ )	Main Terminal Voltage = 3 V <sup>(3)</sup>	MOC3081M			15	mA
			MOC3082M			10	
			MOC3083M			5	
$V_{\text{TM}}$	Peak On-State Voltage, Either Direction	$I_{\text{TM}} = 100\text{ mA peak}$ , $I_F = \text{rated } I_{\text{FT}}$	All		1.8	3.0	V
$I_H$	Holding Current, Either Direction		All		500		$\mu\text{A}$

### Zero Crossing Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{\text{INH}}$	Inhibit Voltage (MT1-MT2 voltage above which device will not trigger)	$I_F = \text{Rated } I_{\text{FT}}$		12	20	V
$I_{\text{DRM2}}$	Leakage in Inhibited State	$I_F = \text{Rated } I_{\text{FT}}$ , $V_{\text{DRM}} = 600\text{ V}$ , off-state			2	mA

### Isolation Characteristics

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{\text{ISO}}$	Isolation Voltage <sup>(4)</sup>	$f = 60\text{ Hz}$ , $t = 1\text{ Minute}$	4170			$V_{\text{ACRMS}}$
$R_{\text{ISO}}$	Isolation Resistance	$V_{\text{I-O}} = 500\text{ V}_{\text{DC}}$		$10^{11}$		$\Omega$
$C_{\text{ISO}}$	Isolation Capacitance	$V = 0\text{ V}$ , $f = 1\text{ MHz}$		0.2		pF

#### Notes:

- Test voltage must be applied within dv/dt rating.
- This is static dv/dt. See Figure 11 for test circuit. Commutating dv/dt is a function of the load-driving thyristor(s) only.
- All devices are guaranteed to trigger at an  $I_F$  value less than or equal to max  $I_{\text{FT}}$ . Therefore, recommended operating  $I_F$  lies between max  $I_{\text{FT}}$  (15 mA for MOC3081M, 10 mA for MOC3082M, 5 mA for MOC3083M) and absolute maximum  $I_F$  (60 mA).
- Isolation voltage,  $V_{\text{ISO}}$ , is an internal device dielectric breakdown rating. For this test, pins 1 and 2 are common, and pins 4, 5 and 6 are common.

### Typical Performance Curves

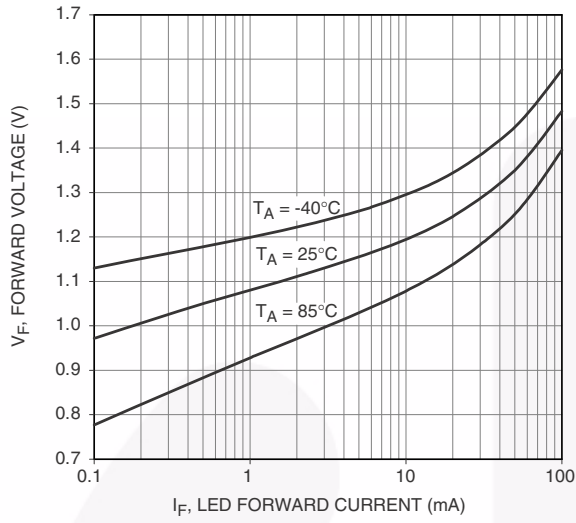


Figure 3. LED Forward Voltage vs. Forward Current

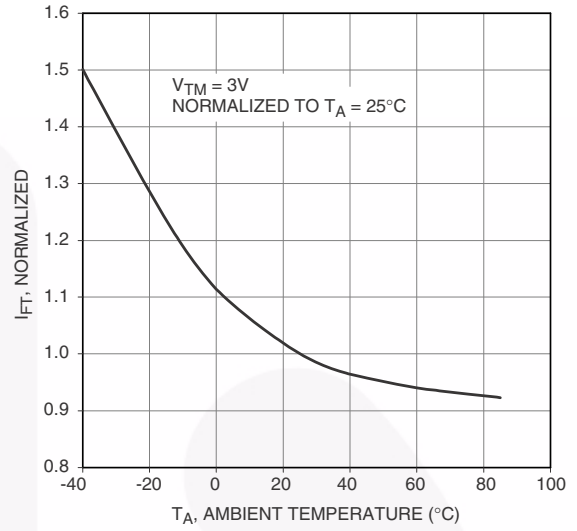


Figure 4. Trigger Current vs. Temperature

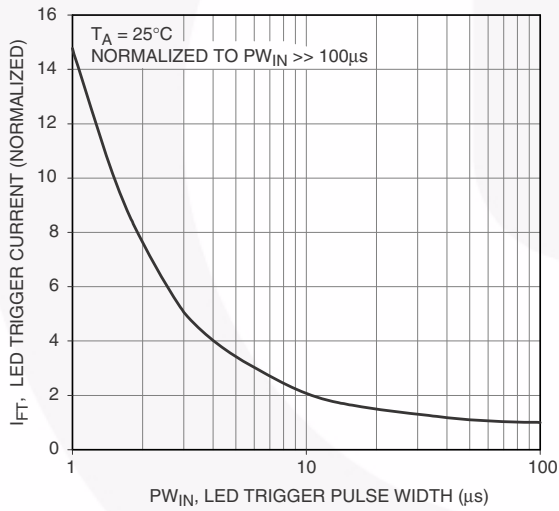


Figure 5. LED Current Required to Trigger vs. LED Pulse Width

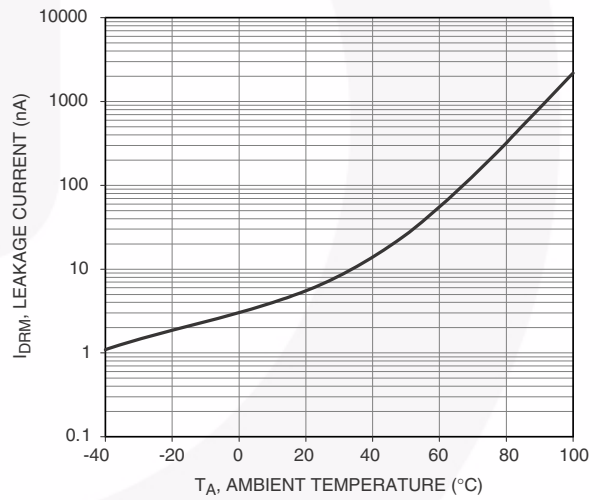
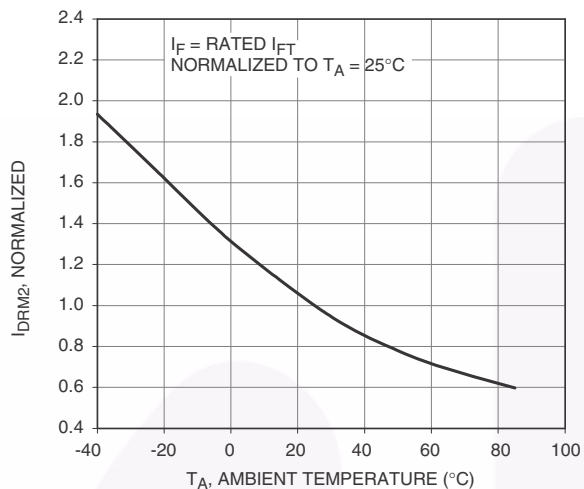
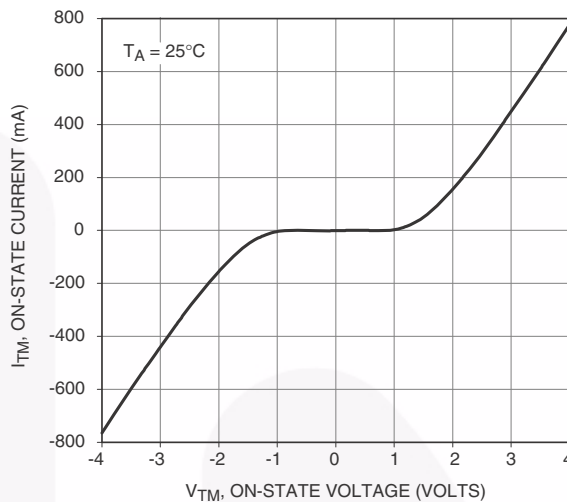


Figure 6. Leakage Current,  $I_{DRM}$  vs. Temperature

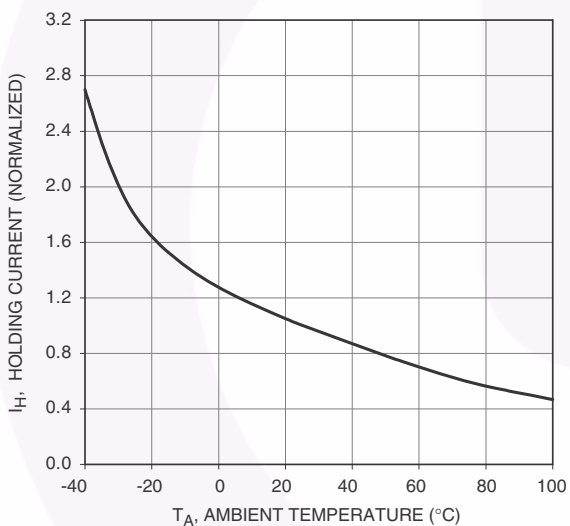
**Typical Performance Curves** (Continued)



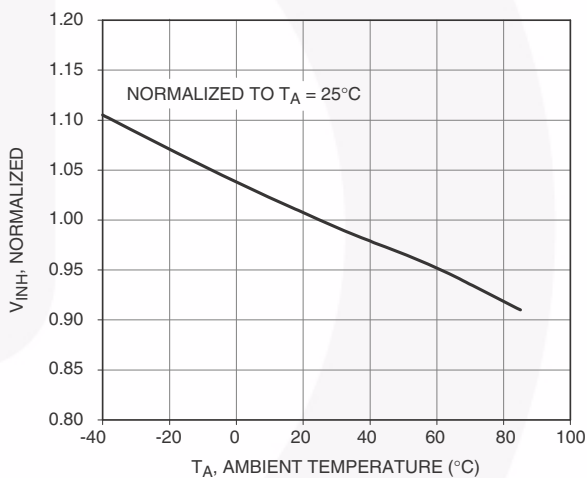
**Figure 7. I<sub>DRM2</sub>, Leakage in Inhibit State vs. Temperature**



**Figure 8. On-State Characteristics**



**Figure 9. I<sub>H</sub>, Holding Current vs. Temperature**



**Figure 10. Inhibit Voltage vs. Temperature**

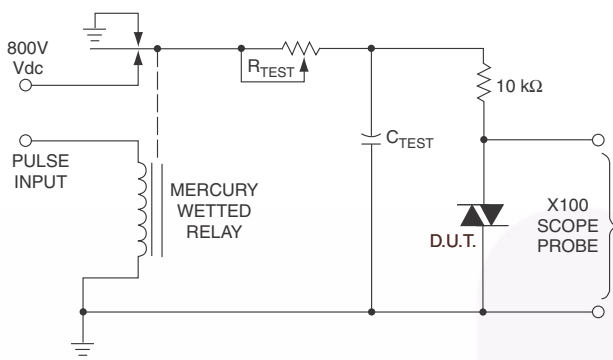


Figure 11. Static dv/dt Test Circuit

1. The mercury wetted relay provides a high speed repeated pulse to the D.U.T.
2. 100x scope probes are used, to allow high speeds and voltages.
3. The worst-case condition for static dv/dt is established by triggering the D.U.T. with a normal LED input current, then removing the current. The variable  $R_{TEST}$  allows the dv/dt to be gradually increased until the D.U.T. continues to trigger in response to the applied voltage pulse, even after the LED current has been removed. The dv/dt is then decreased until the D.U.T. stops triggering.  $\tau_{RC}$  is measured at this point and recorded.

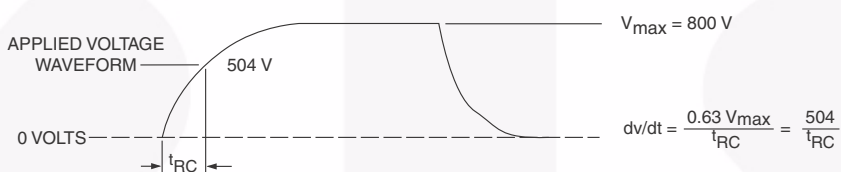
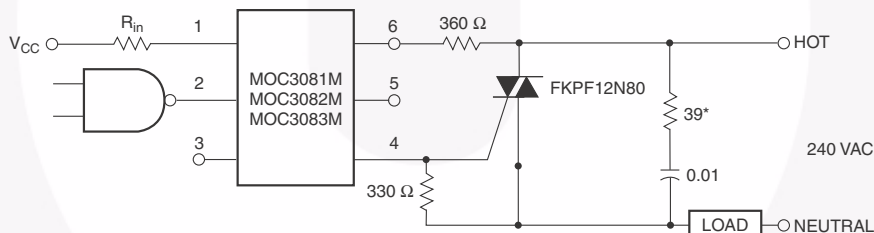


Figure 12. Static dv/dt Test Waveform

Typical circuit for use when hot line switching is required. In this circuit the “hot” side of the line is switched and the load connected to the cold or neutral side. The load may be connected to either the neutral or hot line.

$R_{in}$  is calculated so that  $I_F$  is equal to the rated  $I_{FT}$  of the part, 15 mA for the MOC3081M, 10 mA for the MOC3082M, and 5 mA for the MOC3083M. The 39  $\Omega$  resistor and 0.01  $\mu$ F capacitor are for snubbing of the triac and may or may not be necessary depending upon the particular triac and load use.



\* For highly inductive loads (power factor < 0.5), change this value to 360 $\Omega$ .

Figure 13. Hot-Line Switching Application Circuit

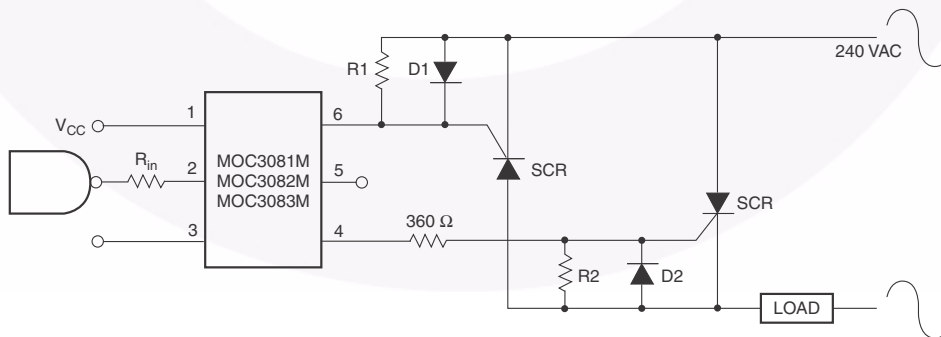


Figure 14. Inverse-Parallel SCR Driver Circuit

Suggested method of firing two, back-to-back SCR's with a Fairchild triac driver. Diodes can be 1N4001; resistors, R1 and R2, are optional 330  $\Omega$ .

**Note:** This optoisolator should not be used to drive a load directly. It is intended to be a trigger device only.



## Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Minimum (T <sub>smin</sub> )	150°C
Temperature Maximum (T <sub>smax</sub> )	200°C
Time (t <sub>s</sub> ) from (T <sub>smin</sub> to T <sub>smax</sub> )	60 seconds to 120 seconds
Ramp-up Rate (T <sub>L</sub> to T <sub>P</sub> )	3°C/second maximum
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 seconds to 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>p</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second maximum
Time 25°C to Peak Temperature	8 minutes maximum

Figure 15. Reflow Profile

## Ordering Information<sup>(5)</sup>

Part Number	Package	Packing Method
MOC3081M	DIP 6-Pin	Tube (50 Units)
MOC3081SM	SMT 6-Pin (Lead Bend)	Tube (50 Units)
MOC3081SR2M	SMT 6-Pin (Lead Bend)	Tape and Reel (1000 Units)
MOC3081VM	DIP 6-Pin, DIN EN/IEC60747-5-5 Option	Tube (50 Units)
MOC3081SVM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tube (50 Units)
MOC3081SR2VM	SMT 6-Pin (Lead Bend), DIN EN/IEC60747-5-5 Option	Tape and Reel (1000 Units)
MOC3081TVM	DIP 6-Pin, 0.4" Lead Spacing, DIN EN/IEC60747-5-5 Option	Tube (50 Units)

### Note:

5. The product orderable part number system listed in this table also applies to the MOC3082M, and MOC3083M, product families.

## Marking Information

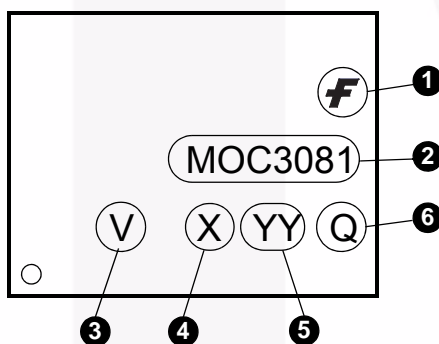


Figure 16. Top Mark

Top Mark Definitions	
1	Fairchild Logo
2	Device Number
3	DIN EN/IEC60747-5-5 Option (only appears on component ordered with this option)
4	One-Digit Year Code, e.g., '5'
5	Two-Digit Work Week, Ranging from '01' to '53'
6	Assembly Package Code



- NOTES:
- A) NO STANDARD APPLIES TO THIS PACKAGE.
  - B) ALL DIMENSIONS ARE IN MILLIMETERS.
  - C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION
  - D) DRAWING FILENAME AND REVISION: MKT-N06BREV4.





LAND PATTERN RECOMMENDATION



NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION
- D) DRAWING FILENAME AND REVISION : MKT-N06CREV4.





NOTES:

- A) NO STANDARD APPLIES TO THIS PACKAGE.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSION
- D) DRAWING FILENAME AND REVISION: MKT-N06Drev4



ON Semiconductor and  are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## PUBLICATION ORDERING INFORMATION

### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor  
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA  
**Phone:** 303-675-2175 or 800-344-3860 Toll Free USA/Canada  
**Fax:** 303-675-2176 or 800-344-3867 Toll Free USA/Canada  
**Email:** [orderlit@onsemi.com](mailto:orderlit@onsemi.com)

**N. American Technical Support:** 800-282-9855 Toll Free  
USA/Canada  
**Europe, Middle East and Africa Technical Support:**  
Phone: 421 33 790 2910  
**Japan Customer Focus Center**  
Phone: 81-3-5817-1050

**ON Semiconductor Website:** [www.onsemi.com](http://www.onsemi.com)  
**Order Literature:** <http://www.onsemi.com/orderlit>  
For additional information, please contact your local  
Sales Representative